

CLAIMS:

1. A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising silicon in contact with a silicon nitride film;

forming a continuous layer of a material including a catalyst capable of promoting a crystallization of silicon onto at least a portion of said semiconductor film;

heating said semiconductor film in order to crystallize said semiconductor film; and then

irradiating said semiconductor film with light in order to improve the crystallinity of said semiconductor film.

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